Application No.: 10/698,466 Docket No.: 8734.033.D1-US

Amendment filed on October 3, 2005 Reply to Office Action dated June 22, 2005

## **AMENDMENTS TO THE SPECIFICATION**

Please amend paragraph [0008] as follows:

[0008] In FIG. 3B, an <u>insulating</u>[[nsulating]] material is deposited on an entire surface of the lower substrate 1 for covering the gate line 2 and the gate electrode 6, thereby forming a gate insulating film 12. First and second semiconductor materials are sequentially deposited on the gate insulating film 12, and subsequently patterned, thereby forming an active layer 14 and an ohmic <u>contact</u>[[contract]] layer 16.